

semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula  $In_xGa_yAl_zN$  where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ , and  $x + y + z = 1$ , wherein the full width at half maximum of the (0004) reflection X-ray rocking curve of said second III-V compound semiconductor is 700 seconds or less regardless of the direction of X-ray incidence, and the compound semiconductor is formed by a vapor phase epitaxy method.

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2. (Twice Amended) A III-V compound semiconductor having a first layer that comprises a first III-V compound semiconductor expressed by the general formula  $In_uGa_vAl_wN$  where  $0 \leq u \leq 1$ ,  $0 \leq v \leq 1$ ,  $0 \leq w \leq 1$ , and  $u + v + w = 1$ , a pattern on said first layer from a material different not only from said first III-V compound semiconductor but also from a second III-V compound semiconductor hereinafter described, and a layer on said first III-V compound semiconductor and said pattern from said second III-V compound semiconductor expressed by the general formula  $In_xGa_yAl_zN$  where  $0 \leq x \leq 1$ ,  $0 \leq y \leq 1$ ,  $0 \leq z \leq 1$ , and  $x + y + z = 1$ , wherein an upper surface of said pattern is not in contact with said second III-V compound semiconductor, and the compound semiconductor is formed by a vapor phase epitaxy method.